

### KTC3203 TRANSISTOR (NPN)

#### FEATURE

Power dissipation

$P_{CM}$ : 0.625 W ( $T_{amb}=25^{\circ}C$ )

Collector current

$I_{CM}$ : 0.8 A

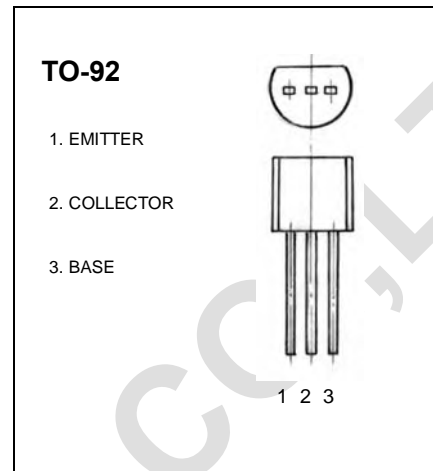
Collector-base voltage

$V_{(BR)CBO}$ : 35 V

Operating and storage junction temperature range

$T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

$T_J$ :  $150^{\circ}C$



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{ mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=35V, I_E=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=100mA$	100		320	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=700mA$	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{ mA}, I_B=20mA$			0.7	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=1V, I_C=10mA$	0.5		0.8	V
Transition frequency	$f_T$	$V_{CE}=5\text{ V}, I_C=10mA$		120		MHz

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320